

Silicon Bridge Rectifiers

TDF30M

Features

- Glass passivated junction
- High surge current capability
- Saves space on printed circuit boards
- High temperature soldering guaranteed:
260°C/10 seconds

- RoHS Compliant

Mechanical Data

- Case: TDF molded plastic
- Molding compound, UL flammability classification rating 94V-0
- Terminals: Solder plated, solderable per MIL- STD-202, Method 208
- Polarity: As marked on body



Maximum Ratings (@T_A = 25°C unless otherwise specified)

Characteristic	Symbol	TDF30M	Units
Peak repetitive reverse voltage	V _{RRM}	1000	V
RMS reverse voltage	V _{RMS}	700	V
DC blocking voltage	V _{DC}	1000	V
Maximum average forward output current	I _{F(AV)}	3.0	A
Peak forward surge current, 8.3ms single half-sine-wave	@T _J = 25°C I _{FSM}	100	A

Thermal Characteristics

Characteristic	Symbol	TDF30M	Units
Typical thermal resistance per leg (Note 1)	R _{θJA}	50	°C/W
	R _{θJC}	10	
Operating junction temperature range	T _J	- 55 ---- + 150	°C
Storage temperature range	T _{STG}	- 55 ---- + 150	°C

Note:

1. Device mounted on PCB with 10 mm x 20 mm x 0.1mm copper pad areas

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Electrical Characteristics (@T_A = 25°C unless otherwise specified)

Parameter	Symbol	Test conditions		Typ.	Max.	Units
Maximum instantaneous forward voltage	V _F	I _F =3.0A Per Diode		--	1.15	V
Maximum Reverse current	I _R	Rated V _R , Per Diode	@T _A =25°C	--	10	μA
			@T _A =125°C	--	200	

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Ratings and Characteristic Curves ($T_A=25^\circ\text{C}$ unless otherwise noted)

Fig.1-Forward Current Derating Curve

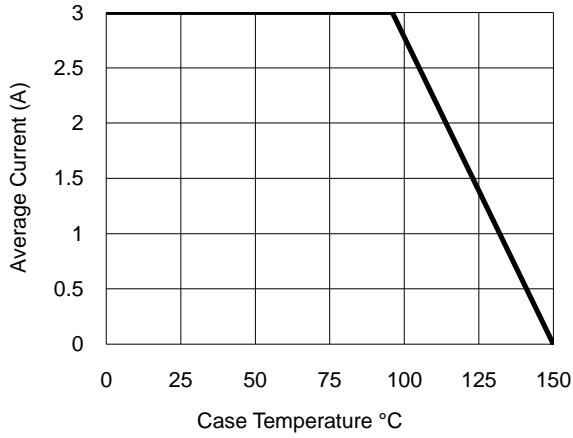


Fig.2- Surge Current Derating Curve

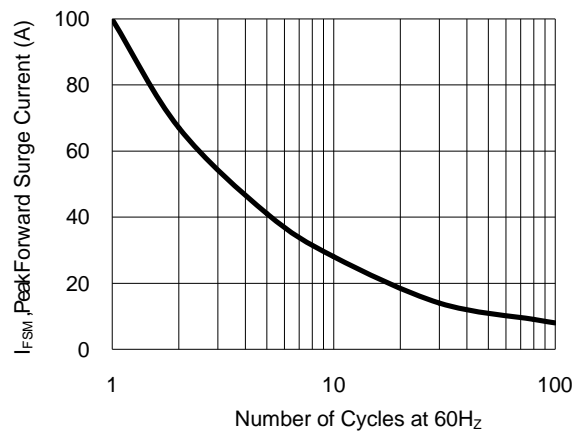


Fig.3- Typical Forward Voltage Characteristic

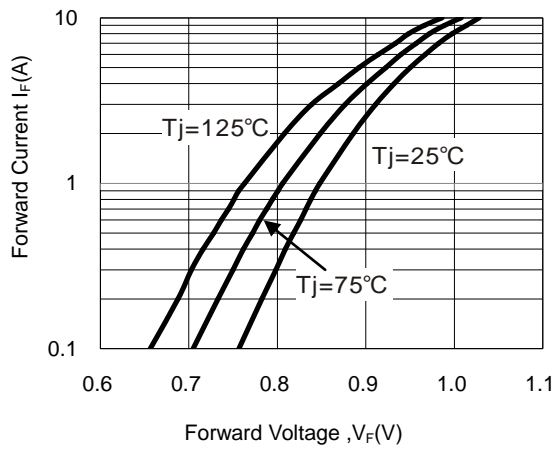
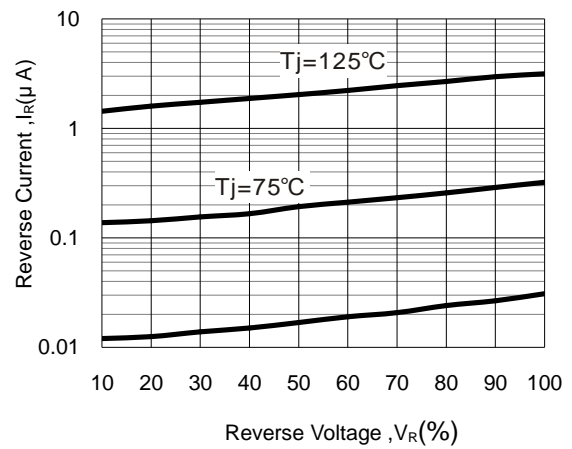


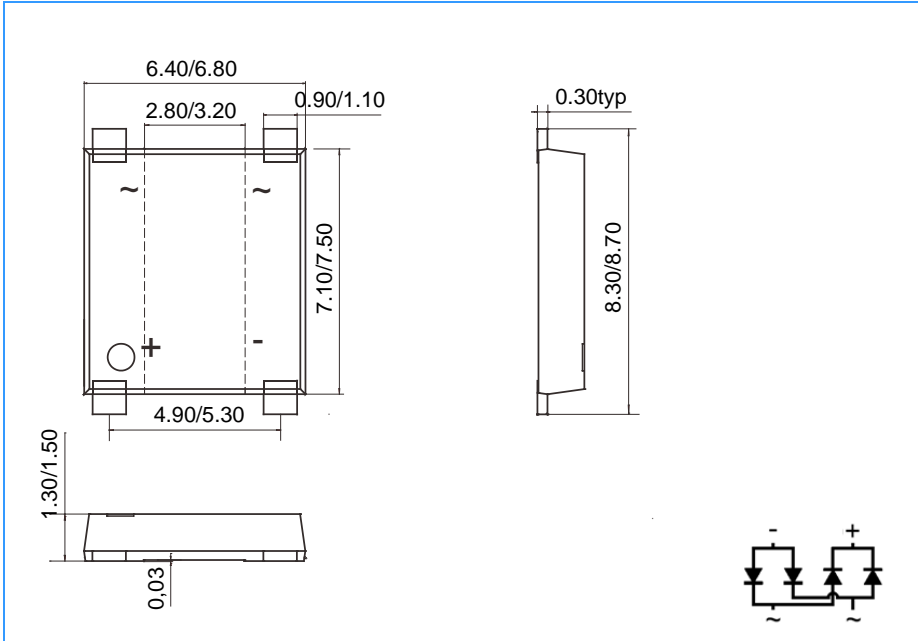
Fig.4- Typical Reverse Characteristic



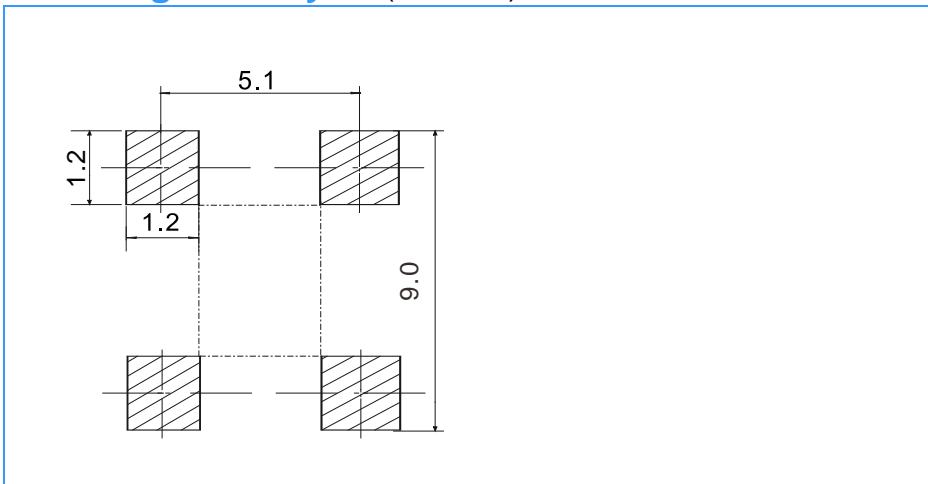
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Package Outline Dimensions(unit:mm)



Mounting Pad Layout(unit:mm)



Ordering Information

Part No.	Marking	Package	Shipping
TDF30M	TDF30M	TDF	3000/Tape&Reel